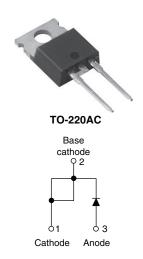


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# HEXFRED® Ultrafast Soft Recovery Diode, 8 A



PRODUCT SUMMARY						
Package	TO-220AC					
I <sub>F(AV)</sub>	8 A					
$V_{R}$	600 V					
V <sub>F</sub> at I <sub>F</sub>	1.4 V					
t <sub>rr</sub> typ.	18 ns					
T <sub>J</sub> max.	150 °C					
Diode variation	Single die					

#### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- Designed and qualified according to JEDEC®-JESD47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





ROHS
COMPLIANT
HALOGEN
FREE
Available

#### **BENEFITS**

- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION**

VS-HFA08TB60... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 8 A continuous current, the VS-HFA08TB60... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TB60... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	$V_R$		600	V		
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	8			
Single pulse forward current	I <sub>FSM</sub>		60	Α		
Maximum repetitive forward current	I <sub>FRM</sub>		24			
Maximum navva discination	P <sub>D</sub>	T <sub>C</sub> = 25 °C	36	W		
Maximum power dissipation		T <sub>C</sub> = 100 °C	14	]		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C		

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# VS-HFA08TB60PbF, VS-HFA08TB60-N3

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<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V <sub>BR</sub>	Ι <sub>R</sub> = 100 μΑ		600	-	-	
		I <sub>F</sub> = 8.0 A		=	1.4	1.7	V
Maximum forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 16 A	See fig. 1	-	1.7	2.1	
		I <sub>F</sub> = 8.0 A, T <sub>J</sub> = 125 °C		-	1.4	1.7	
Maximum reverse	_	V <sub>R</sub> = V <sub>R</sub> rated	Soo fig. 0	-	0.3	5.0	
leakage current	I <sub>RM</sub>	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	See fig. 2	=	100	500	μΑ
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	See fig. 3	=	10	25	pF
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body		-	8.0		nH

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	A/μs, V <sub>R</sub> = 30 V	-	18	-		
Reverse recovery time	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C	$I_F = 8.0 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	37	55	ns	
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	55	90		
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	3.5	5.0	A nC	
reak recovery current	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	4.5	8.0		
Poverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	65	138		
Reverse recovery charge	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	124	360	IIC	
Peak rate of fall of recovery current during t <sub>b</sub>	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		240	-	Λ/μο		
	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		_	210	-	- A/µs	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	3.5		
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	K/W	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-		
Weight			-	2.0	-	g	
vveignt			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-220AC		HFA08TB60			

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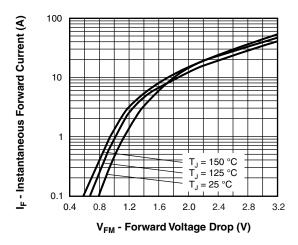


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

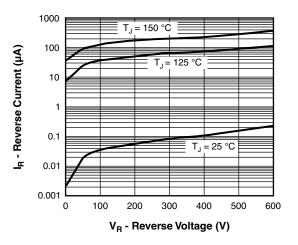


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

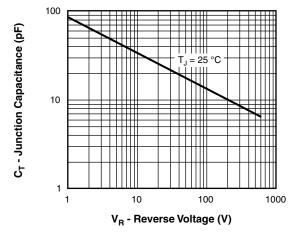


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

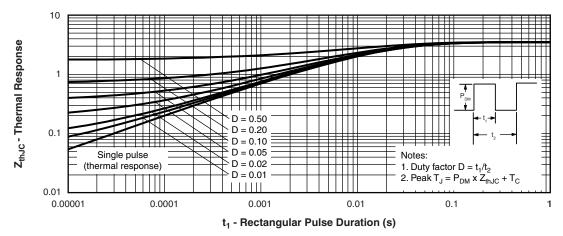


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics





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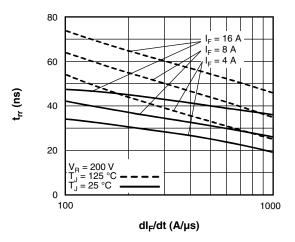


Fig. 5 - Typical Reverse Recovery Time vs. dI<sub>E</sub>/dt

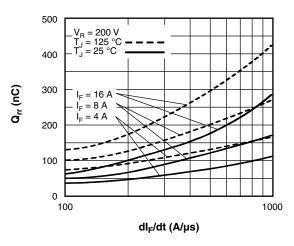


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

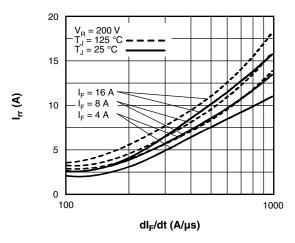


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

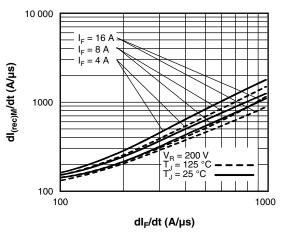


Fig. 8 - Typical  $dI_{(rec)M}/dt$  vs.  $dI_F/dt$ 

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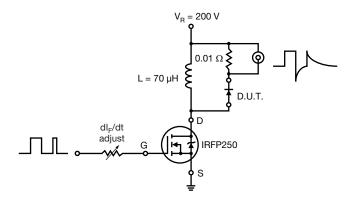
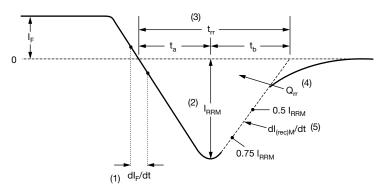


Fig. 9 - - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\rm Q_{rr}$  area under curve defined by  $\rm t_{rr}$  and  $\rm I_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 10 - Reverse Recovery Waveform and Definitions

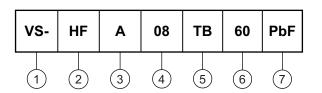


## VS-HFA08TB60PbF, VS-HFA08TB60-N3

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#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

- HEXFRED® family

Electron irradiated

- Current rating (08 = 8 A)

5 - Package:

TB = TO-220AC

Voltage rating (60 = 600 V)

7 - Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-HFA08TB60PbF	50	1000	Antistatic plastic tube				
VS-HFA08TB60-N3	50	1000	Antistatic plastic tube				

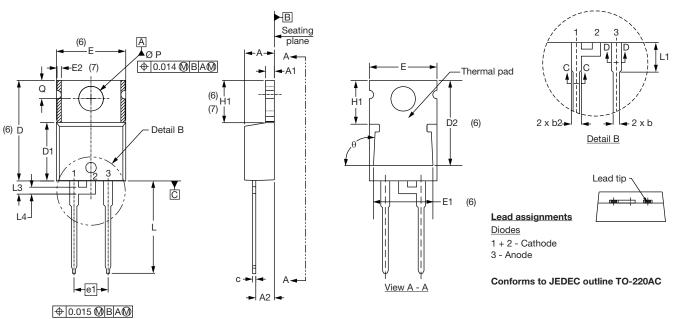
LINKS TO RELATED DOCUMENTS					
Dimensions		www.vishay.com/doc?95221			
Dort marking information	TO-220ACPbF	www.vishay.com/doc?95224			
Part marking information	TO-220AC-N3	www.vishay.com/doc?95068			



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### **TO-220AC**

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIM	IETERS	INCHES		NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
Е	10.11	10.51	0.398	0.414	3, 6

SYMBOL	MILLIM	IETERS	INC	HES	NOTES	
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
E1	6.86	8.89	0.270	0.350	6	
E2	-	0.76	-	0.030	7	
е	2.41	2.67	0.095	0.105		
e1	4.88	5.28	0.192	0.208		
H1	6.09	6.48	0.240	0.255	6, 7	
L	13.52	14.02	0.532	0.552		
L1	3.32	3.82	0.131	0.150	2	
L3	1.78	2.13	0.070	0.084		
L4	0.76	1.27	0.030	0.050	2	
ØΡ	3.54	3.73	0.139	0.147		
Q	2.60	3.00	0.102	0.118		
θ	90° t	o 93°	90° t	o 93°		

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline

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